

Data Sheet

Linear Field Sensors

KMY20, KMY21, KMZ20



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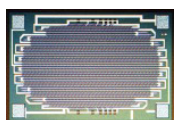
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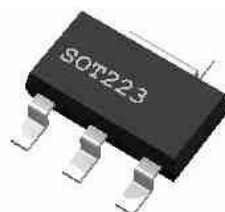
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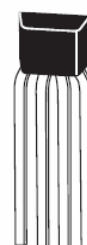
| FEATURES | APPLICATIONS |
|--|--|
| <ul style="list-style-type: none"> • output proportional to magnetic field strength with very high sensitivity • very small hysteresis • large operating temperature range, from -40°C up to +150 °C • highly reliable • with / without internal magnet | <ul style="list-style-type: none"> • detection of very weak magnetic fields, like earth magnetic field, or field generated by small magnetic particles • detection of objects that distort non-local magnetic fields • revolution measurement on ferro-magnetic gears • contactless switch / displacement sensor |
| DIES & PACKAGES | |



dies **MR174B, MRHB**

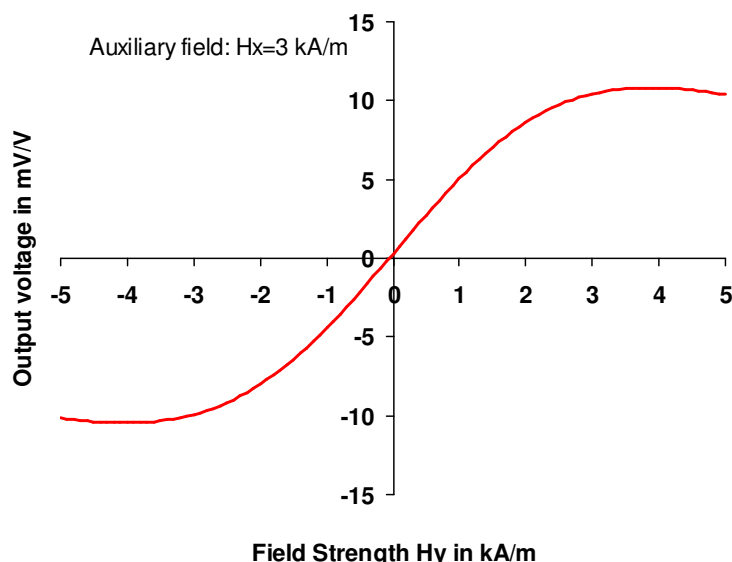
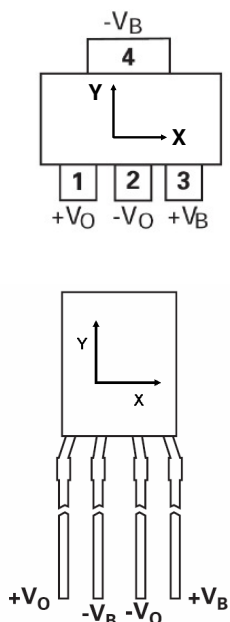


KMY20M



E-Line
KMZ20M

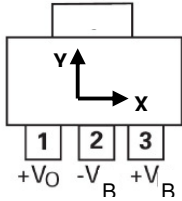
KMY20 / KMZ20M



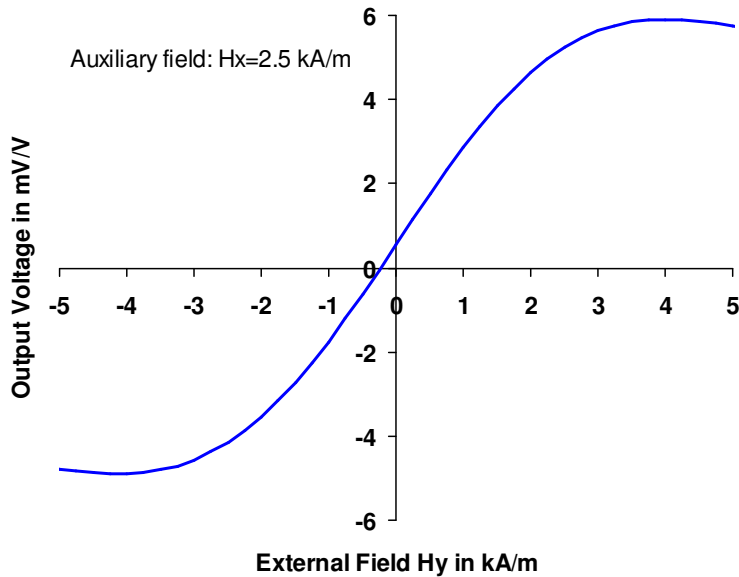
The **KMY** and **KMZ** sensors are highly sensitive magnetic field sensors which utilize the anisotropic magnetoresistance effect. The **KMY20** and **KMZ20** sensors contain a Wheatstone bridge.

KMY21

In contrast to the KMY20 sensor products, the **KMY21M** consists of a half bridge, making the sensor well suited for dynamic measurements.



It contains an internal magnet, which provides an auxiliary field of approx. 2.5 kA/m.



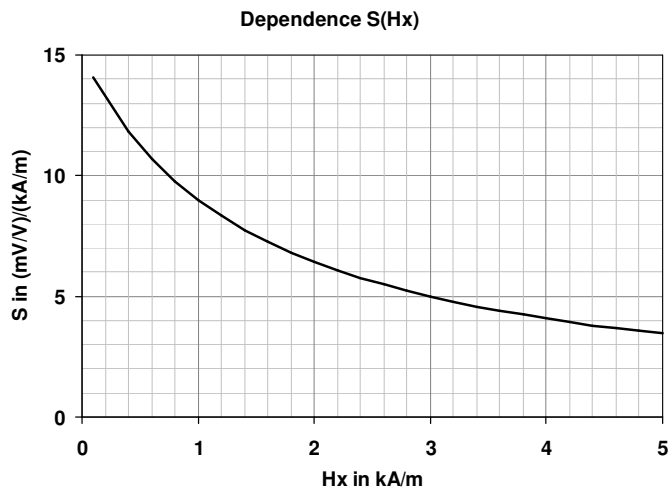
GENERAL DESCRIPTION

Due to its featured properties - high sensitivity and almost no hysteresis – the **KMY / KMZ** sensors are used in a wide range of applications, like magnetic field measurement, revolution counters, proximity detecting, position measurement.

An uniaxial linear magnetic field in y-direction will generate a linear output within the specified magnetic field range. The sensor is available in two types: the **KMY20 M** and **KMZ20 M** sensor types contain intrinsic magnets which provide an auxiliary magnetic field at the sensor die which prevents magnetic domains from flipping irregularly.

If the dies **MR174B** and **MRHB** or the **KMY20 S** are used, the auxiliary field has to be provided by the user. The dependence of the sensitivity with auxiliary field strength is depicted in the figure.

Auxiliary field strengths below $H_x < 1.5$ kA/m are not recommended, as small disturbances may flip the magnetization domains. Sometimes, the magnetic conditions in the application may provide enough H_x bias field stabilization.



CHARACTERISTIC VALUES

| PARAMETER | SYMBOL | CONDITION | MIN | TYP | MAX | UNIT |
|--------------------------------------|--------------|------------------|-------|-------|-------|--------|
| Operating Limits | | | | | | |
| max. supply voltage | $V_{cc,max}$ | | | | 10 | V |
| max. current | $I_{cc,max}$ | SOT223 E-Line | | | 9 | mA |
| operating temperature | T_{op} | SOT223, E-Line | -40 | | +150 | °C |
| storage temperature | T_{st} | SOT223, E-Line | -40 | | +150 | °C |
| General Sensor Specifications | | | | | | |
| TC of amplitude | $TCSV$ | Condition A, C | -0.36 | -0.32 | -0.28 | %/K |
| TC of resistance | $TCBR$ | Condition A, C | +0.27 | +0.32 | +0.37 | %/K |
| TC of offset | $TCVoff$ | Condition A, C | -4 | 0 | +4 | μV/V/K |

Sensor Specifications KMY20, KMZ20 (T=25 °C, Hx=3 kA/m)

| PARAMETER | SYMBOL | CONDITION | MIN | TYP | MAX | UNIT |
|---------------------|---------------------|----------------|------|------|------|-----------|
| Supply voltage | V_{cc} | Condition A, B | | 5 | | V |
| Bridge resistance | R_b | Condition A, B | 1200 | 1700 | 2200 | Ω |
| Output signal range | $\Delta V_o/V_{cc}$ | Condition A, B | 16 | 20 | 24 | mV/V |
| Offset voltage | V_{off}/V_{cc} | Condition A, B | -1 | 0 | +1 | mV/V |
| Sensitivity | S | Condition A, B | 3.7 | 4.7 | 5.7 | mV/V/kA/m |
| Hysteresis | V_H/V_{cc} | Condition A, B | - | - | 50 | μV/V |

Sensor Specifications KMY21M (T=25 °C, Hx=2.5 kA/m)

| PARAMETER | SYMBOL | CONDITION | MIN | TYP | MAX | UNIT |
|---------------------|---------------------|----------------|------|------|------|-----------|
| Supply voltage | V_{cc} | Condition A, B | | 5 | | V |
| Bridge resistance | R_b | Condition A, B | 1100 | 1500 | 1900 | Ω |
| Output signal range | $\Delta V_o/V_{cc}$ | Condition A, B | 8 | 9.5 | 12 | mV/V |
| Offset voltage | V_{off}/V_{cc} | Condition A, B | 48 | 50 | 52 | %Vcc |
| Sensitivity | S | Condition A, B | 2.05 | 2.50 | 3.10 | mV/V/kA/m |
| Hysteresis | V_H/V_{cc} | Condition A, B | - | - | 50 | μV/V |

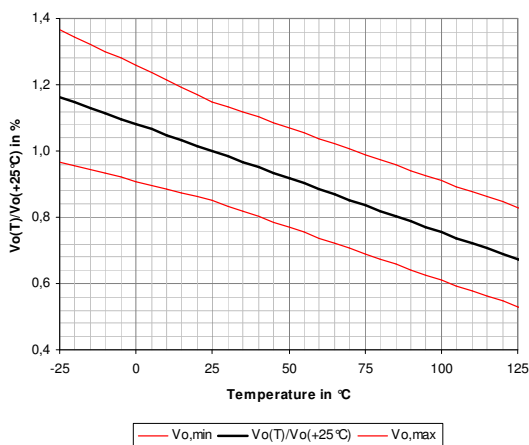
Stress above one or more of the limiting values may cause permanent damage to the device. Exposure to limiting values for extended periods may affect device reliability.

MEASUREMENT CONDITIONS

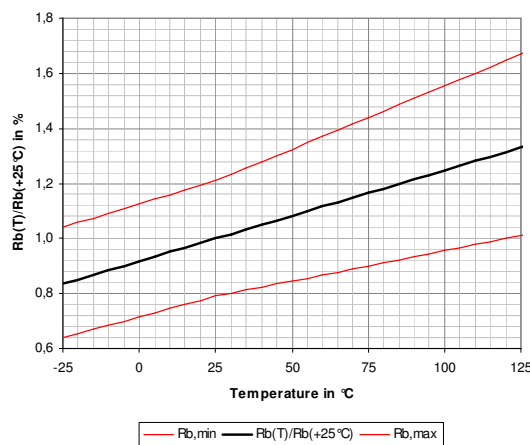
| PARAMETER | SYMBOL | UNIT | CONDITION |
|---|-----------------------------------|---|---|
| Condition A: Set Up Conditions | | | |
| Ambient temperature | T | °C | 23±5 |
| Supply voltage | V _{cc} | V | 5 |
| Output voltage | V _O | mV | V _O =(V _{O+} -V _{O-}) |
| | V _O /V _{cc} | mV/V | output voltages are also given independently on supply voltage: example: V _O /V _{cc} =(V _{O+} -V _{O-})/V _{cc} |
| Reference half bridge | | | measure MR half bridge against reference half bridge 2* 2 kΩ 0.1% |
| for full bridge sensors (KMY20S, KMY20M, KMZ20S, KMZ20M) | | for half bridge sensors (KMY21M) | |
| | | | |
| | | <p>The output voltage of the MR half bridge is measured against a reference half bridge</p> | |
| Condition B: Sensor Specifications (T=23±5 °C, H_x=3.0±0.5 kA/m) | | | |
| Output voltage range | ΔV _O /V _{cc} | mV/V | H _y = -7...+7 kA/m; ΔV _O = (V _{O,max} - V _{O,min}) |
| Offset voltage | V _{off} /V _{cc} | mV/V | H _y = 0; V _{off} = V _O (H _y) |
| Sensitivity | S | (mV/V)/(kA/m) | H _y = 1kA/m; S := $\frac{V_0(+H_y) - V_0(-H_y)}{2 \cdot V_{cc}}$ |
| Hysteresis | V _H /V _{cc} | μV/V | H _y in kA/m (V _O (H _y = 0; H _y = -1 → +1) - V _O (H _y = 0; H _y = +1 → -1))/V _{cc} |

| PARAMETER | SYMBOL | UNIT | CONDITION |
|---|--------|----------|--|
| C. Sensor Specifications (T=-25 °C, +125 °C) | | | |
| Ambient temperatures | T | °C | T ₁ =-25 °C, T ₀ =+25 °C, T ₂ =+125 °C |
| TC of amplitude | TCSV | %/K | $TCV = \frac{1}{(T_2 - T_1)} \cdot \frac{\Delta V_0 / V_{cc}(T_2) - \Delta V_0 / V_{cc}(T_1)}{\Delta V_0 / V_{cc}(T_1)} \cdot 100\%$ |
| TC of resistance | TCBR | %/K | $TCR = \frac{1}{(T_2 - T_1)} \cdot \frac{R(T_2) - R(T_1)}{R(T_1)} \cdot 100\%$ |
| TC of offset | TCVoff | (μV/V)/K | $TCVoff = \frac{V_{off}(T_2) - V_{off}(T_1)}{(T_2 - T_1)}$ |

TEMPERATURE DEPENDENCIES



signal amplitude related to room temperature value



bridge resistance related to room temperature value

LEGAL DISCLAIMER

This product is not designed for use in life support appliances, devices or systems where malfunction of this product can reasonably be expected to result in personal injury. HL Planartechnik GmbH customers using or selling this product for use in such applications do so at their own risk and agree to fully indemnify HL Planartechnik GmbH for any damages resulting from such improper use or sale.

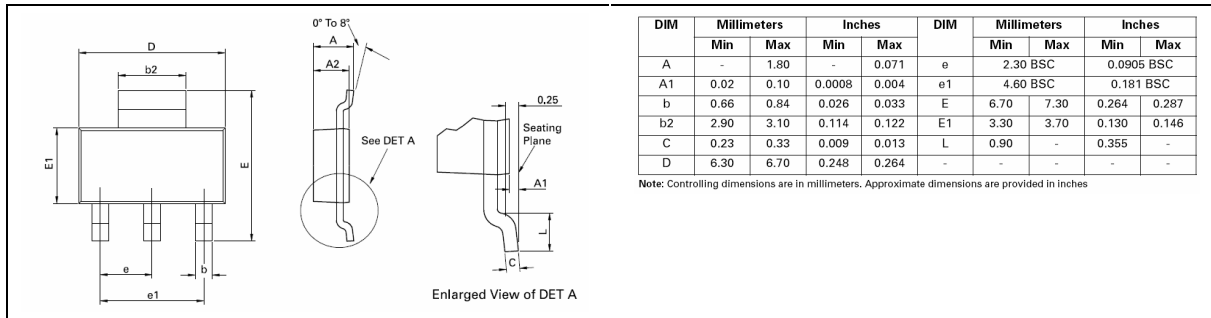
This data sheet contains target specifications for product development which may be subject to changes without notice.

PACKAGES

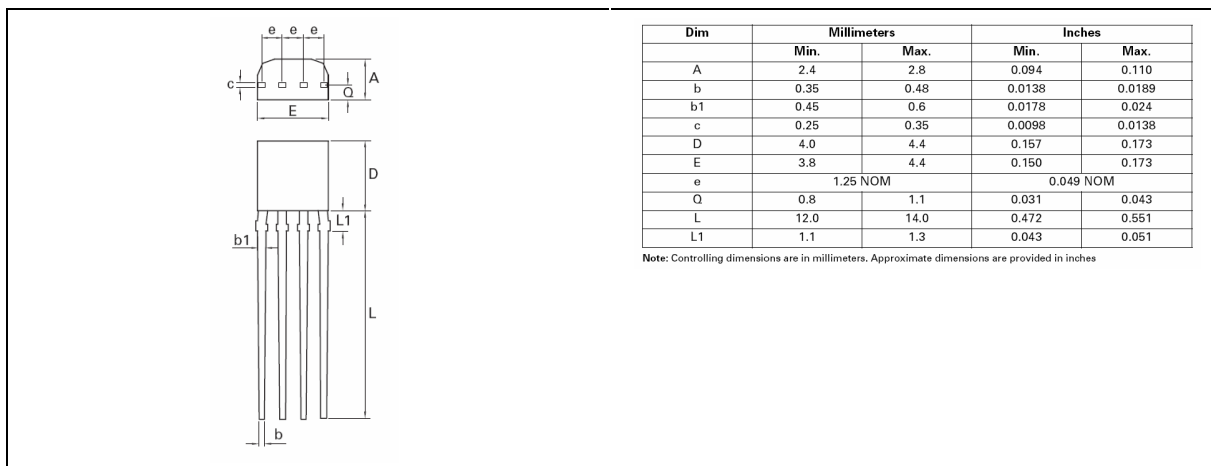
DIE LAYOUT

Die layout and dimensions on request.

SOT223



E-LINE 4 PIN



ORDERING

| DEVICE | DIE | PACKAGE | INTERNAL MAGNET | PART NUMBER |
|----------|-------------|---------|-----------------|-------------|
| MR174B | full bridge | wafer | n/a | G-MRCH-002 |
| MRHB | half bridge | wafer | n/a | G-MRCH-009 |
| KMY 20 S | full bridge | SOT-223 | NO | G-MRCH-006 |
| KMY 20 M | full bridge | SOT-223 | YES | G-MRCH-001 |
| KMY 21 M | half bridge | SOT-223 | YES | G-MRCH-011 |
| KMZ 20 S | full bridge | E-Line | NO | G-MRCH-007 |
| KMZ 20 M | full bridge | E-Line | YES | G-MRCH-003 |